

Supplementary Information

Effect of Manganese Alloying on Infrared Detectors Made of $\text{Pb}_{1-x}\text{Mn}_x\text{Te}/\text{CdTe}$ Multilayer Composite

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Figure

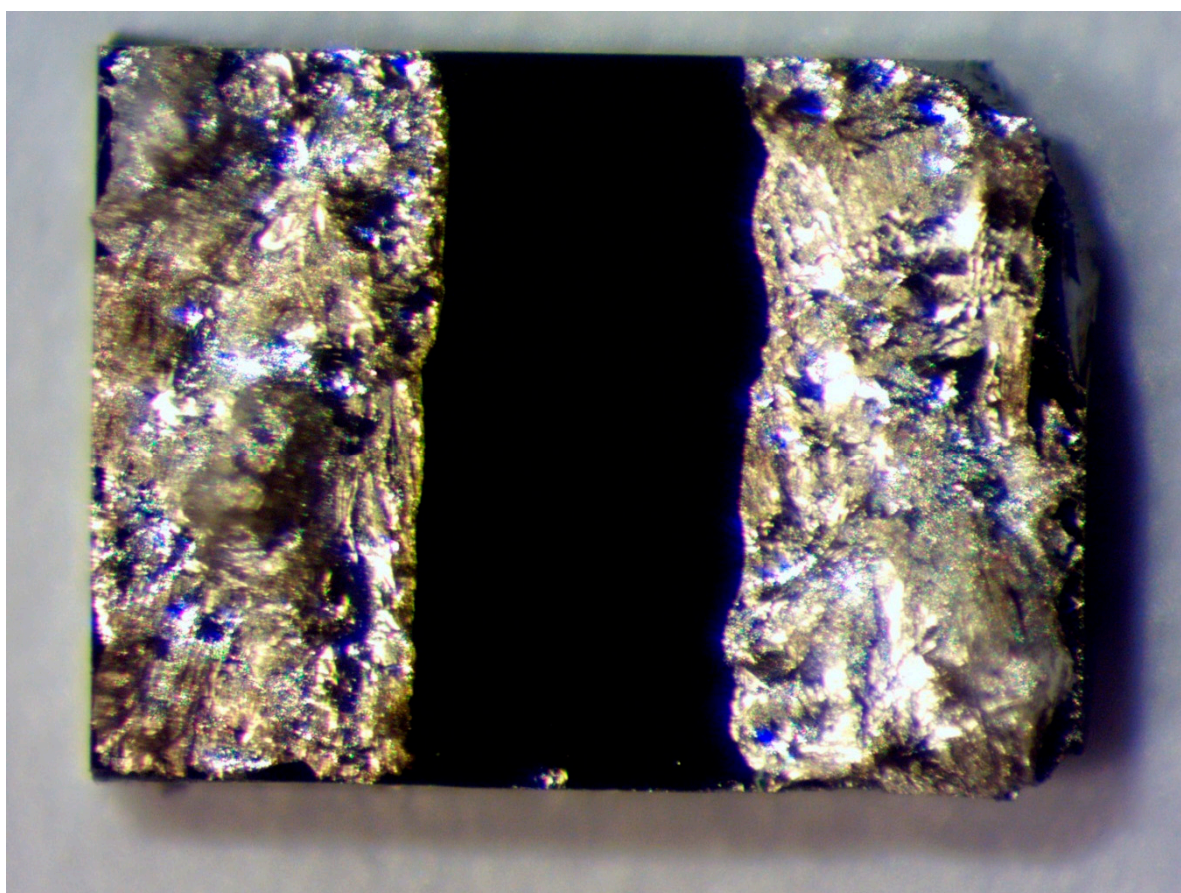


Figure S1. Picture of the fabricated typical photoresistor

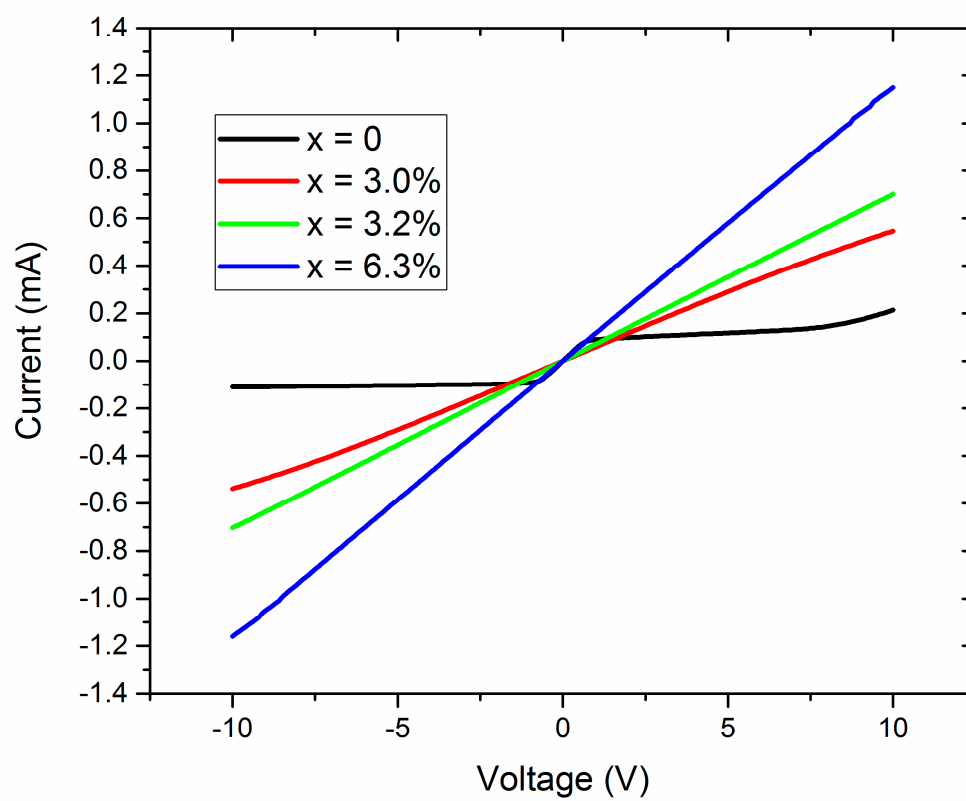


Figure S2. Current-voltage characteristics of fabricated photoresistors